

ABSTRACT OF THE DISCLOSURE

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The present invention is directed to a semiconductor device having a gate electrode ^{includes} comprised of a plurality of sidewalls, each having a recess formed therein. The present invention is also directed to a method of forming a semiconductor device. In one illustrative embodiment, the method comprises forming a layer of dopant material in a layer of polysilicon and etching the layer of polysilicon to define a gate electrode having a plurality of sidewalls, each of which have a recess formed therein.

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